



IRF840AL Information



For Reference Only

Part Number IRF840AL

Manufacturer Vishay Siliconix

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 500V 8A TO-262

Package TO-262-3 Long Leads, I2Pak, TO-262AA

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IRF840AL Specifications

Manufacturer Part Number IRF840AL Manufacturer Vishay Siliconix Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-262-3 Long Leads, 12Pak, TO-262AA Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 500V Current - Continuous Drain (Id) @ 25°C 8A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 38nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1018pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 3.1W (Ta), 125W (Tc) Rds On (Max) @ Id, Vgs 850 mOhm @ 4.8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package 12PAK Package / Case TO-262-3 Long Leads, 12Pak, TO-262AA		
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Series-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C8A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs38nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1018pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)3.1W (Ta), 125W (Tc)Rds On (Max) @ Id, Vgs850 mOhm @ 4.8A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device Package12PAKPackage / CaseTO-262-3 Long Leads, 12Pak, TO-262AA		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 8A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 850 mOhm @ 4.8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package 12PAK Package / Case N-Channel NOSFET (Metal Oxide) NOSFET (Metal Oxide) 8A (Tc) 10V NOV 8A (Tc) 10V Vg (250μA 1018pF @ 25V 1	Package	TO-262-3 Long Leads, I2Pak, TO-262AA
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C8A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs38nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1018pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)3.1W (Ta), 125W (Tc)Rds On (Max) @ Id, Vgs850 mOhm @ 4.8A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device Package12PAKPackage / CaseTO-262-3 Long Leads, 12Pak, TO-262AA	Series	-
Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C8A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs38nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1018pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)3.1W (Ta), 125W (Tc)Rds On (Max) @ Id, Vgs850 mOhm @ 4.8A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device Package12PAKPackage / CaseTO-262-3 Long Leads, 12Pak, TO-262AA	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA 38nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 850 mOhm @ 4.8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case TO-262-3 Long Leads, 12Pak, TO-262AA	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs38nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1018pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)3.1W (Ta), 125W (Tc)Rds On (Max) @ Id, Vgs850 mOhm @ 4.8A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device Package12PAKPackage / CaseTO-262-3 Long Leads, 12Pak, TO-262AA	Drain to Source Voltage (Vdss)	500V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) As Son (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case 4V @ 250μA 38nC @ 10V 1018pF @ 25V 25V 25V 25V 25V 25V 25V 25V	Current - Continuous Drain (Id) @ 25°C	8A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Mounting Type Through Hole Supplier Device Package Fakage / Case TO-262-3 Long Leads, 12Pak, TO-262AA	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Storm Temperature Supplier Device Package Package / Case 1018pF @ 25V	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 3.1W (Ta), 125W (Tc) Rds On (Max) @ Id, Vgs 850 mOhm @ 4.8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package I2PAK Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Gate Charge (Qg) (Max) @ Vgs	38nC @ 10V
FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 850 mOhm @ 4.8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package I2PAK Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Input Capacitance (Ciss) (Max) @ Vds	1018pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 850 mOhm @ 4.8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package I2PAK Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs 850 mOhm @ 4.8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package I2PAK Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package I2PAK Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Power Dissipation (Max)	3.1W (Ta), 125W (Tc)
Mounting Type Through Hole Supplier Device Package I2PAK Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Rds On (Max) @ Id, Vgs	850 mOhm @ 4.8A, 10V
Supplier Device Package I2PAK Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Mounting Type	Through Hole
	Supplier Device Package	I2PAK
Report errors?	Package / Case	TO-262-3 Long Leads, I2Pak, TO-262AA
		Report errors?

IRF840AL Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRF840AL Payment Methods





















IRF840AL Shipping Methods













If you have any question about IRF840AL, please do not hesitate to contact us!

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